

Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG. 7)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150^\circ\text{C}$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				70	
I_H	$I_T=100\text{mA}$		MAX.	45	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150^\circ\text{C}$		MIN.	1200	V/s
$(dI/dt)_c$	$(dV/dt)_c=9\text{V}/\mu\text{s}$ $V_j=150^\circ\text{C}$		MIN.	3	A/ms
t_{on}	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	3	s
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=8.5A$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^\circ\text{C}$	0.8	V
R_D	Dynamic resistance	$T_j=150^\circ\text{C}$	63	P
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	A
I_{RRM}		$T_j=150^\circ\text{C}$	0.8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
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ORDERING INFORMATION

<u>T</u>	<u>06</u>	<u>35</u>	<u>H</u>	<u>-6</u>	<u>F</u>
Triacs					F:TO-220F(Ins)
<u>IT(RMS):6A</u>					
	<u>35:IGT1-3 035 mA</u>			<u>6:VDRM /VRRM 1600 V</u>	
			<u>High junction temperature</u>		

MARKING

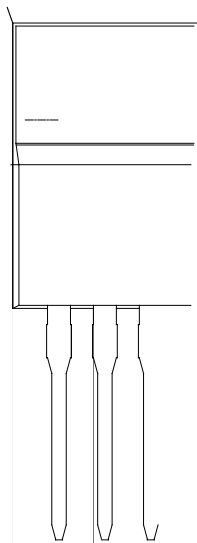


FIG.1: Maximum power dissipation versus RMS on-state current

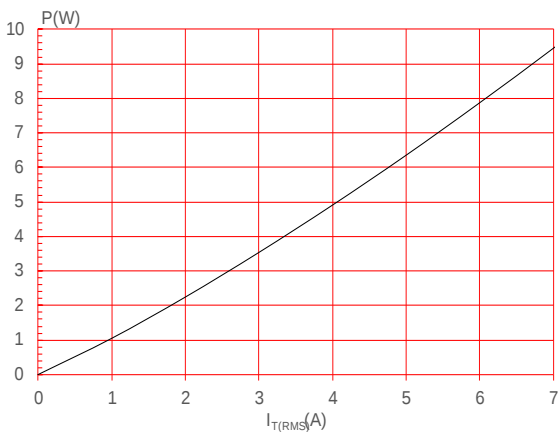


FIG.2: RMS on-state current versus case temperature

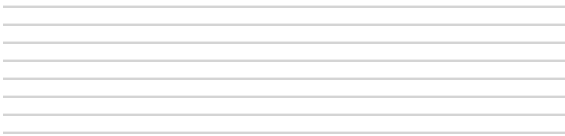
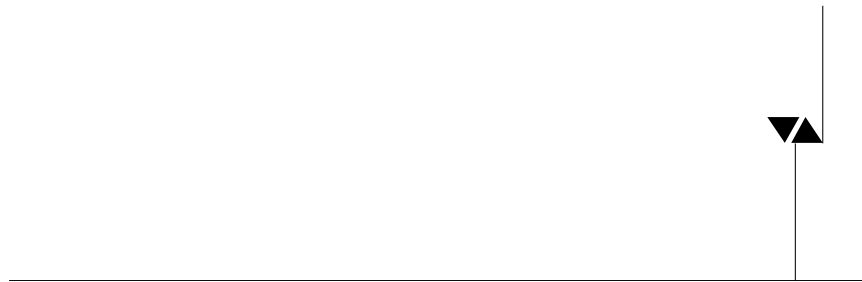


FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards 61000



ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(Ma)	Package	Base qty. (pcs)	Delivery mode
		- -			
T0635H-6F	600	35	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated
Oct.11, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

T0635H-6F

